

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the present application.

### **Listing of Claims:**

**Claim 1 (currently amended):** A gallium-nitride semiconductor substrate onto which a light-emitting-device-forming film has been epitaxially grown, characterized by photoluminescent emission from the device-forming film under a predetermined monochromatic beam correlating to a metal-atom density level of  $10 \times 10^{11}$  atoms/cm<sup>2</sup> or less on ~~that metal contamination on the substrate surface is  $10 \times 10^{11}$  atoms/cm<sup>2</sup> or less on~~ the GaN substrate surface.

**Claim 2 (currently amended):** A gallium-nitride semiconductor substrate onto which a light-emitting-device-forming film has been epitaxially grown, characterized by photoluminescent emission from the device-forming film under a predetermined monochromatic beam correlating to a metal-atom density level of  $5 \times 10^{11}$  atoms/cm<sup>2</sup> or less on ~~that metal contamination on the substrate surface is  $5 \times 10^{11}$  atoms/cm<sup>2</sup> or less on~~ the GaN substrate surface.

**Claim 3 (currently amended):** A method of processing a gallium-nitride semiconductor substrate ~~having a complex of faces in which Ga is exposed and faces in which N is exposed,~~ the method comprising:

providing a gallium-nitride semiconductor substrate having a complex front side in which the Ga and N faces are exposed in alternation;

polishing the substrate front side with an abrasive embedded into a metallic

platen, thereby ~~leaving~~ transforming the substrate episurface into a process-transformed layer ~~on the substrate~~;

reactive-ion etching the substrate front side using a halogen plasma to remove the process-transformed layer; and

wet etching the reactive-ion etched substrate, by means of an etchant that is one of HF + H<sub>2</sub>O<sub>2</sub>, HCl + H<sub>2</sub>O<sub>2</sub>, H<sub>2</sub>SO<sub>4</sub> + H<sub>2</sub>O<sub>2</sub>, HNO<sub>3</sub> + H<sub>2</sub>O<sub>2</sub>, HF + O<sub>3</sub>, HCl + O<sub>3</sub>, H<sub>2</sub>SO<sub>4</sub> + O<sub>3</sub>, HNO<sub>3</sub>, or HNO<sub>3</sub> + O<sub>3</sub>, and that has an oxidation-reduction potential of more than 1.2 V, in a room-temperature aqueous solution of pH = 2 to 3, ~~not~~ selective for either the Ga or the N faces of the substrate, yet does have metal etching capability, and an oxidation-reduction potential of more than 1.2 V, thereby to remove contaminant metal produced by said reactive-ion etching.

**Claim 4 (canceled)**

**Claim 5 (previously presented):** A method of processing a gallium-nitride semiconductor substrate as set forth in claim 3, characterized in that a wash for taking off organic matter by means of an organic solvent, and a wash by means of an alkaline solution in order to take off nonmetal contaminants are carried out either before or after the wet etching.

**Claim 6-10 (canceled)**